FS6183-04

1 PLL Clock Generator IC

1.0 Features

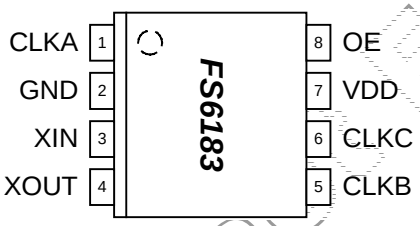
- Three output clock frequencies
- Output enable function
- Crystal oscillator tunable with external varactor
- 3.3V supply voltage (contact factory for 5V)
- Low phase noise, low jitter
- Small circuit board footprint (8-pin 0.150″ SOIC)
- Special high transconductance crystal oscillator suitable for external varactor VCXO function if desired
- Custom frequency selections available - contact your local AMI Sales Representative for more information

2.0 Description

The FS6183 is a monolithic CMOS clock generator IC designed to minimize cost and component count in digital video/audio systems.

A high-resolution phase-locked loop generates three output clocks (CLKA, CLKB, & CLKC) through an array of post-dividers. All frequencies are ratiometrically derived from the crystal frequency. The locking of all the output frequencies together can eliminate unpredictable artifacts in video systems.

Figure 1: Pin Configuration



8-pin (0.150″) SOIC

Table 1: Crystal / Output Frequencies

DEVICE	f_{XIN} (MHz)	CLKA (MHz)	CLKB (MHz)	CLKC (MHz)
FS6183-04	14.31818	24.576 -0.66ppm	24.576 -0.66ppm	24.576 -0.66ppm

NOTE: Contact AMI for custom PLL frequencies and 5 volt operation

Figure 2: Block Diagram

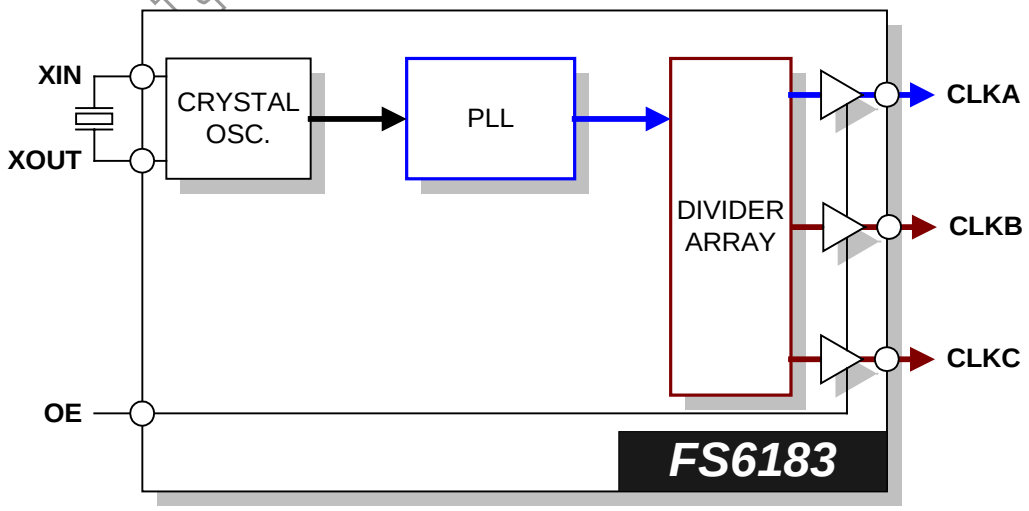


Table 2: Pin Descriptions

Key: AI = Analog Input; AO = Analog Output; DI = Digital Input; DI^U = Input with Internal Pull-Up; DI_D = Input with Internal Pull-Down; DIO = Digital Input/Output; DI-3 = Three-Level Digital Input, DO = Digital Output; P = Power/Ground; # = Active Low pin

PIN	TYPE	NAME	DESCRIPTION
1	DO	CLKA	Clock Output A
2	P	GND	Ground
3	AI	XIN	Crystal Oscillator Feedback
4	AO	XOUT	Crystal Oscillator Drive
5	DO	CLKB	Clock Output B
6	DO	CLKC	Clock Output C
7	P	VDD	Power Supply (+3.3V)
8	DI^U	OE	Output Enable

3.0 Functional Block Description

3.1 Phase-Locked Loop (PLL)

The on-chip PLLs are a standard frequency- and phase-locked loop architecture. The PLL multiplies the reference oscillator to the desired frequency by a ratio of integers. The frequency multiplication is exact with a zero synthesis error.

3.2 Crystal Oscillator

The oscillator operates the crystal resonator in the parallel-resonant mode.

4.0 Electrical Specifications

Table 3: Absolute Maximum Ratings

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. These conditions represent a stress rating only, and functional operation of the device at these or any other conditions above the operational limits noted in this specification is not implied. Exposure to maximum rating conditions for extended conditions may affect device performance, functionality, and reliability.

PARAMETER	SYMBOL	MIN.	MAX.	UNITS
Supply Voltage (V_{SS} = ground)	V_{DD}	V_{SS}-0.5	7	V
Input Voltage, dc	V_I	V_{SS}-0.5	V_{DD}+0.5	V
Output Voltage, dc	V_O	V_{SS}-0.5	V_{DD}+0.5	V
Input Clamp Current, dc (V_I < 0 or V_I > V_{DD})	I_{IK}	-50	50	mA
Output Clamp Current, dc (V_I < 0 or V_I > V_{DD})	I_{OK}	-50	50	mA
Storage Temperature Range (non-condensing)	T_S	-65	150	°C
Ambient Temperature Range, Under Bias	T_A	-55	125	°C
Junction Temperature	T_J		125	°C
Lead Temperature (soldering, 10s)			260	°C
Input Static Discharge Voltage Protection (MIL-STD 883E, Method 3015.7)			2	kV

CAUTION: ELECTROSTATIC SENSITIVE DEVICE

Permanent damage resulting in a loss of functionality or performance may occur if this device is subjected to a high-energy electrostatic discharge.

Table 4: Operating Conditions

PARAMETER	SYMBOL	CONDITIONS/DESCRIPTION	MIN.	TYP.	MAX.	UNITS
Supply Voltage	V_{DD}	3.3V ± 10%	3.0	3.3	3.6	V
Ambient Operating Temperature Range	T_A		0		70	°C

Table 5: DC Electrical Specifications

Unless otherwise stated, V_{DD} = 3.3V ± 10%, no load on any output, and ambient temperature range T_A = 0°C to 70°C. Parameters denoted with an asterisk (*) represent nominal characterization data and are not production tested to any specific limits. Where given, MIN and MAX characterization data are ± 3σ from typical. Negative currents indicate current flows out of the device.

PARAMETER	SYMBOL	CONDITIONS/DESCRIPTION	MIN.	TYP.	MAX.	UNITS
Overall						
Supply Current, Dynamic, with Loaded Outputs	I_{DD}	f_{XTAL} = 13.5MHz; C_L = 10pF		20		mA
Crystal Oscillator						
Crystal Resonator Frequency	f_{XTAL}	Fundamental Mode	-	13.5	-	MHz
Crystal Loading Capacitance	$C_{L(xtal)}$	As seen by a crystal connected to XIN and XOUT		17		pF
Crystal Oscillator Drive Transconductance	gm_{OSC}	VDD = 3.3V		16		mSiemens
Oscillator Source Current	I_{OH}	VDD = 3.3V V(XIN) = 0V, V(XOUT) = 0V		-18		mA
Oscillator Sink Current	I_{OL}	VDD = 3.3V V(XIN) = VDD, V(XOUT) = VDD		23		mA
Clock Outputs (CLKA, CLKB, CLKC)						
High-Level Output Source Current *	I_{OH}	V_O = 2.0V		40		mA
Low-Level Output Sink Current *	I_{OL}	V_O = 0.4V		17		mA
Output Impedance *	z_{OH}	V_O = 0.5V_{DD}; output driving high		25		Ω
	z_{OL}	V_O = 0.5V_{DD}; output driving low		25		
Short Circuit Source Current *	I_{OSH}	V_O = 0V; shorted for 30s, max.		-55		mA
Short Circuit Sink Current *	I_{OSL}	V_O = 3.3V; shorted for 30s, max.		55		mA

Table 6: AC Timing Specifications

Unless otherwise stated, V_{DD} = 3.3V ± 10%, no load on any output, and ambient temperature range T_A = 0°C to 70°C. Parameters denoted with an asterisk (*) represent nominal characterization data and are not production tested to any specific limits. Where given, MIN and MAX characterization data are ± 3σ from typical.

PARAMETER	SYMBOL	CONDITIONS/DESCRIPTION	CLOCK (MHz)	MIN.	TYP.	MAX.	UNITS
Clock Outputs (CLKx)							
Duty Cycle *		t_{hi} / t_{clk}; Measured at V_{DD}/2		45		55	%
Jitter, Absolute Period (pk-pk) *	$t_{j(\Delta P)}$	From rising edge to next rising edge at V_{DD}/2, C_L = 10pF			300		ps
Jitter, RMS Long Term ($\sigma_y(\tau)$) *	$t_{j(LT)}$	From 0-500µs at V_{DD}/2, C_L = 10pF compared to ideal clock source			150		ps
Rise Time *	t_r	V_{DD} = 3.3V; V_O = 0.3V to 3.0V; C_L = 10pF			1		ns
Fall Time *	t_f	V_{DD} = 3.3V; V_O = 3.0V to 0.3V; C_L = 10pF			1		ns
Output Frequency Synthesis Error		(unless otherwise noted in Frequency Table)				0	ppm

5.0 Package Information

Table 7: 8-pin SOIC (0.150") Package Dimensions

	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.061	0.068	1.55	1.73
A1	0.004	0.0098	0.102	0.249
A2	0.055	0.061	1.40	1.55
B	0.013	0.019	0.33	0.49
C	0.0075	0.0098	0.191	0.249
D	0.189	0.196	4.80	4.98
E	0.150	0.157	3.81	3.99
e	0.050 BSC		1.27 BSC	
H	0.230	0.244	5.84	6.20
h	0.010	0.016	0.25	0.41
L	0.016	0.035	0.41	0.89
Θ	0°	8°	0°	8°

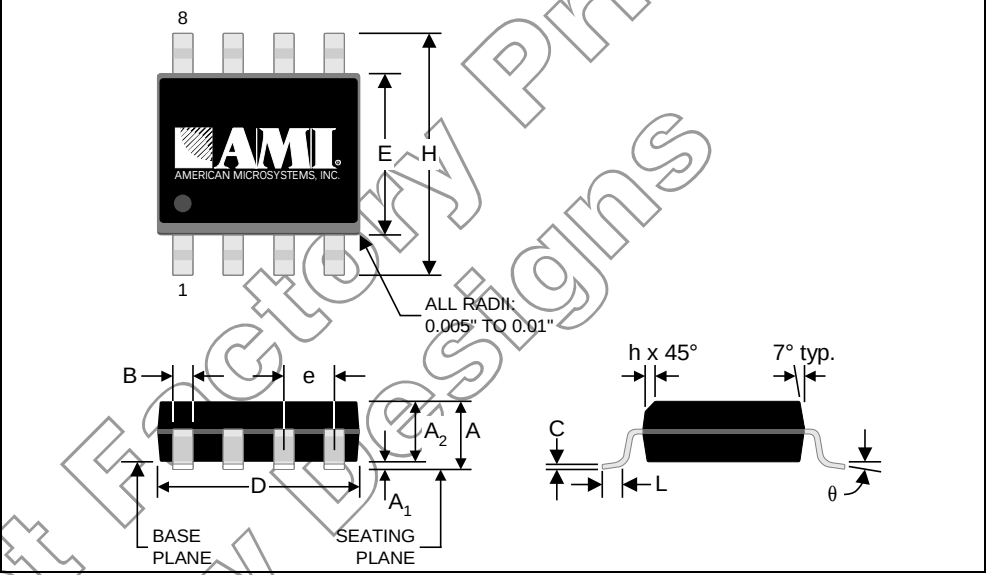


Table 8: 8-pin SOIC (0.150") Package Characteristics

PARAMETER	SYMBOL	CONDITIONS/DESCRIPTION	TYP.	UNITS
Thermal Impedance, Junction to Free-Air 8-pin 0.150" SOIC	Θ_{JA}	Air flow = 0 m/s	110	°C/W
Lead Inductance, Self	L_{11}	Corner lead	2.0	nH
		Center lead	1.6	
Lead Inductance, Mutual	L_{12}	Any lead to any adjacent lead	0.4	nH
Lead Capacitance, Bulk	C_{11}	Any lead to V_{SS}	0.27	pF

6.0 Ordering Information

ORDERING CODE	DEVICE NUMBER	PACKAGE TYPE	OPERATING TEMPERATURE RANGE	SHIPPING CONFIGURATION
11640-842	FS6183-04	8-pin (0.150") SOIC (Small Outline Package)	0°C to 70°C (Commercial)	Tape and Reel

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